

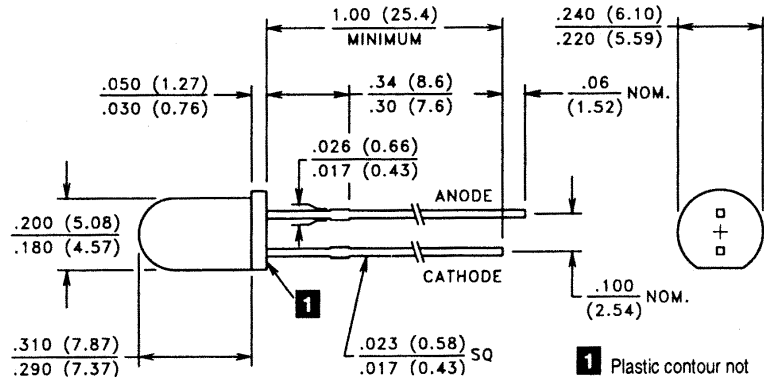
GaAlAs Infrared Emitting Diodes

T-1¾ (5 mm) Plastic Package — 880 nm

VTE1261, 1262



PACKAGE DIMENSIONS inch (mm)



CASE 26 T-1¾ (5 mm)
CHIP SIZE: .018" x .018"

DESCRIPTION

This narrow beam angle 5 mm diameter plastic packaged emitter contains a large area, double wirebonded, GaAlAs, 880 nm, high efficiency IRED chip suitable for higher current pulse applications.

ABSOLUTE MAXIMUM RATINGS @ 25°C (unless otherwise noted) ■

Maximum Temperatures		Maximum Reverse Voltage:	5.0V
Storage and Operating:	-40°C to 100°C	Maximum Reverse Current @ $V_R = 5V$:	10 μA
Continuous Power Dissipation:	200 mW	Peak Wavelength (Typical):	880 nm
Derate above 30°C:	2.86 mW/°C	Junction Capacitance @ 0V, 1 MHz (Typ.):	35 pF
Maximum Continuous Current:	100 mA	Response Time @ $I_F = 20$ mA	
Derate above 30°C:	1.43 mA/°C	Rise: 1.0 μs Fall: 1.0 μs	
Peak Forward Current, 10 μs , 100 pps:	3.0 A	Lead Soldering Temperature:	260°C
Temp. Coefficient of Power Output (Typ.):	-8%/°C	(1.6 mm from case, 5 seconds max.)	

ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also GaAlAs curves, pages 108-110)

Part Number ■	Output						Forward Drop		Half Power Beam Angle	
	Irradiance				Radiant Intensity	Total Power	Test Current	V_F		
	E_e		Condition		I_e	P_O	I_{FT}	@ I_{FT}	$\theta_{1/2}$	
	mW/cm ²		distance	Diameter	mW/sr	mW	mA (Pulsed)	Volts		Typ.
	Min.	Typ.	mm	mm	Min.	Typ.		Typ.	Max.	
VTE1261	3.0	3.9	36	6.4	39	20	100	1.5	2.0	$\pm 10^\circ$
VTE1262	4.0	5.2	36	6.4	52	25	100	1.5	2.0	$\pm 10^\circ$

■ Refer to General Product Notes, page 2.

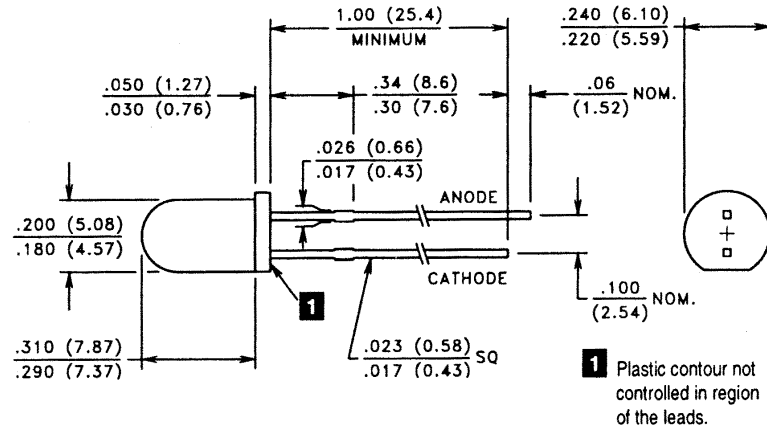
GaAlAs Infrared Emitting Diodes

T-1 $\frac{3}{4}$ (5 mm) Plastic Package — 880 nm

VTE1281-1, -2



PACKAGE DIMENSIONS inch (mm)



CASE 26 T-1 $\frac{3}{4}$ (5 mm)
CHIP SIZE: .015" x .015"

DESCRIPTION

This narrow beam angle 5 mm diameter plastic packaged emitter contains a medium area, single wirebonded, GaAlAs, 880 nm, high efficiency IRED chip. It is designed to be cost effective in moderate pulse drive applications.

ABSOLUTE MAXIMUM RATINGS @ 25°C (unless otherwise noted) ■

Maximum Temperatures									
Storage and Operating:	-40°C to 100°C	Maximum Reverse Voltage:	5.0V						
Continuous Power Dissipation:	200 mW	Maximum Reverse Current @ $V_R = 5V$:	10 μA						
Derate above 30°C:	2.86 mW/°C	Peak Wavelength (Typical):	880 nm						
Maximum Continuous Current:	100 mA	Junction Capacitance @ 0V, 1 MHz (Typ.):	23 pF						
Derate above 30°C:	1.43 mA/°C	Response Time @ $I_F = 20$ mA							
Peak Forward Current, 10 μs , 100 pps:	2.5 A	Rise: 1.0 μs Fall: 1.0 μs							
Temp. Coefficient of Power Output (Typ.):	-8%/°C	Lead Soldering Temperature:	260°C						
		(1.6 mm from case, 5 seconds max.)							

ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also GaAlAs curves, pages 108-110)

Part Number ■	Output						Forward Drop		Half Power Beam Angle	
	Irradiance		Radiant Intensity	Total Power	Test Current	V_F				
	E_e		Condition	I_e	P_O	I_{FT}	@ I_{FT}			
	mW/cm ²						Volts			
	Min.	Typ.	distance	Diameter	Min.	Typ.	mA (Pulsed)	Typ.	Max.	Typ.
VTE1281-1	2.5	3.3	36	6.4	32	20	100	1.5	2.0	$\pm 10^\circ$
VTE1281-2	5.0	6.5	36	6.4	65	25	100	1.5	2.0	$\pm 10^\circ$

■ Refer to General Product Notes, page 2.